

ECAT Physics Chapter 18 Electronics Online Test

| Sr | Questions | Answers Choice |
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| 1 | Electric lines of force | A. Intersect each other B. Are always parallel C. Are always anti-parallel D. Never intersect E. None of these |
| 2 | The electric field lines start from | A. Positive charge B. Negative charge C. Either A or B D. Neutron E. An atom |
| 3 | The SI unit of charge is | A. Ampere B. Watt C. Coulomb D. Volt E. Joule |
| 4 | The intensity at a point due to a charge is inversely proportional to | A. Amount of charge B. Size of the charge C. Distance between charge and the point D. Square of the distance from the charge E. None of these |
| 5 | Electric intensity at a place due to a charged conductor is a | A. Scalar quantity B. Vector quantity C. Semi vector and semi scalar D. Dimensionless quantity E. Both A and D are true |
| 6 | Electric field strength is defined as | A. Work done on unit charge B. Force exerted on unit charge C. Distance covered by unit charge D. Power exerted by unit charge E. None of these |
| 7 | Michael Faraday is known by his work on | A. Nuclear strong force B. Gravitational force C. Nuclear weak force D. Electric force E. None of these |
| 8 | The concept of electric field theory was introduced by | A. Michael Faraday B. Newton C. Dalton D. Kepler E. Einstein |
| 9 | Origin of the electric and the gravitational forces | A. Was known in 1911 A.D. B. Was known in 1811 A.D. C. Was known in 1711 A.D. D. is still unknown E. Was known in 1611 A.D. |
| 10 | If the distance between two charges is doubled, the force between them will become | A. Double B. Half C. Three times D. One fourth E. One third |
| 11 | In a transistor, collector current is controlled by | A. Collector voltage B. Base current C. Collector resistance D. All of the above |
| 12 | Most of the electrons in the base of an NPN transistor flow | A. Out of the base leadB. Into the collectorC. Into the emitD. Into the base supply |
| 13 | When transistors are used in digital circuits they usually operate in the | A. Active region B. Breakdown region C. Saturation and cutoff regions |

| | | D. Linear region |
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| 14 | Improper biasing of a transistor circuit produces | A. Heavy loading of emitter current B. Distortion in the output signal C. Excessive heat at collector terminal D. Faulty location of load line |
| 15 | The reverse saturation current in a PN junction diode is only due to | A. Majority carriers B. Minority Carriers C. Acceptor ions D. Donor ions |